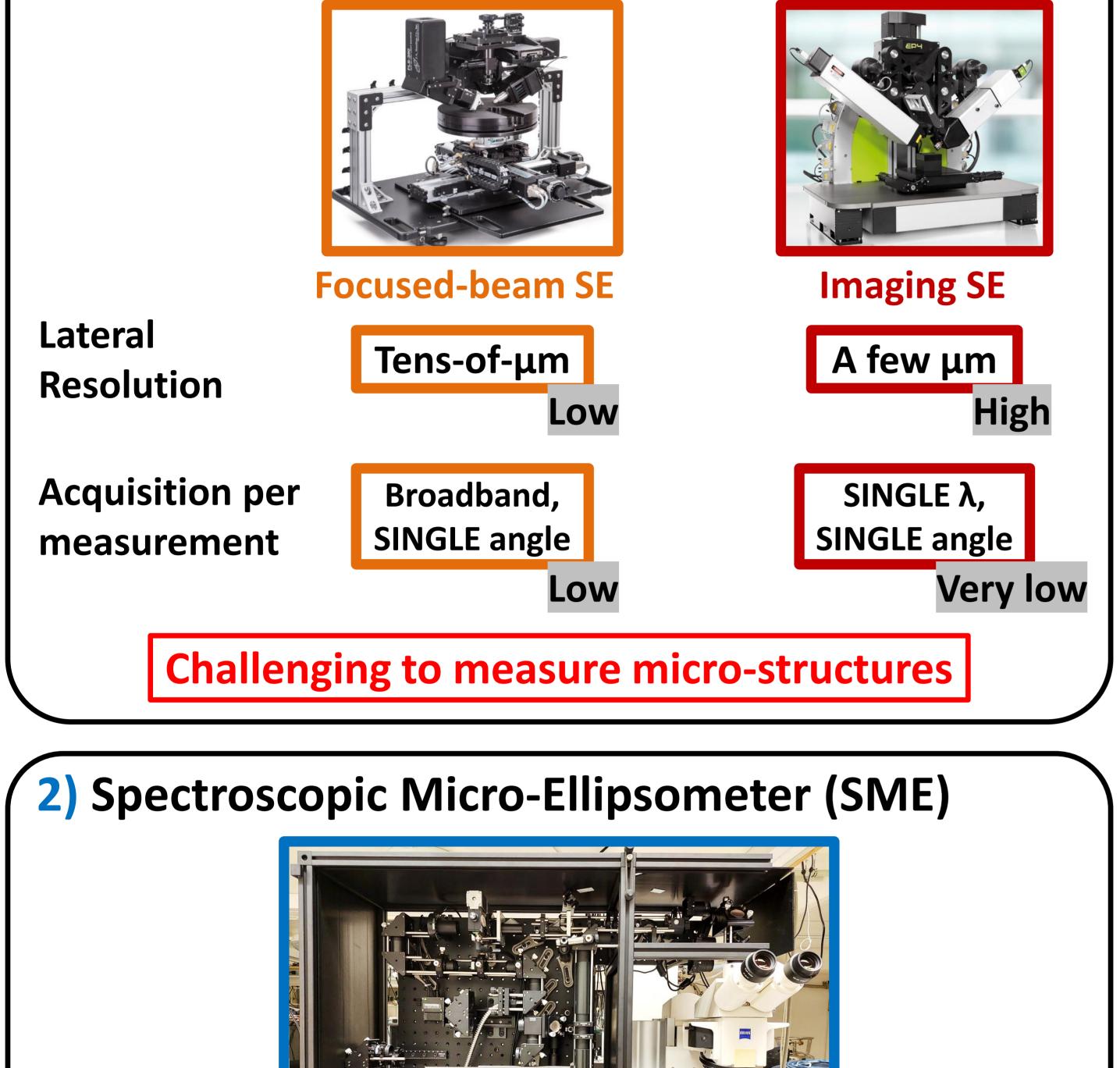
Thickness mapping and layer number identification of exfoliated van der Waals materials by Fourier imaging micro-ellipsometry <u>Ralfy Kenaz<sup>1</sup></u>, Saptarshi Ghosh<sup>1</sup>, Pradheesh Ramachandran<sup>1</sup>, Kenji Watanabe<sup>2</sup>, Takashi Taniguchi<sup>2</sup>, Hadar Steinberg<sup>1</sup>, Ronen Rapaport<sup>1</sup> <sup>1</sup> The Racah Institute of Physics, The Hebrew University of Jerusalem, Israel

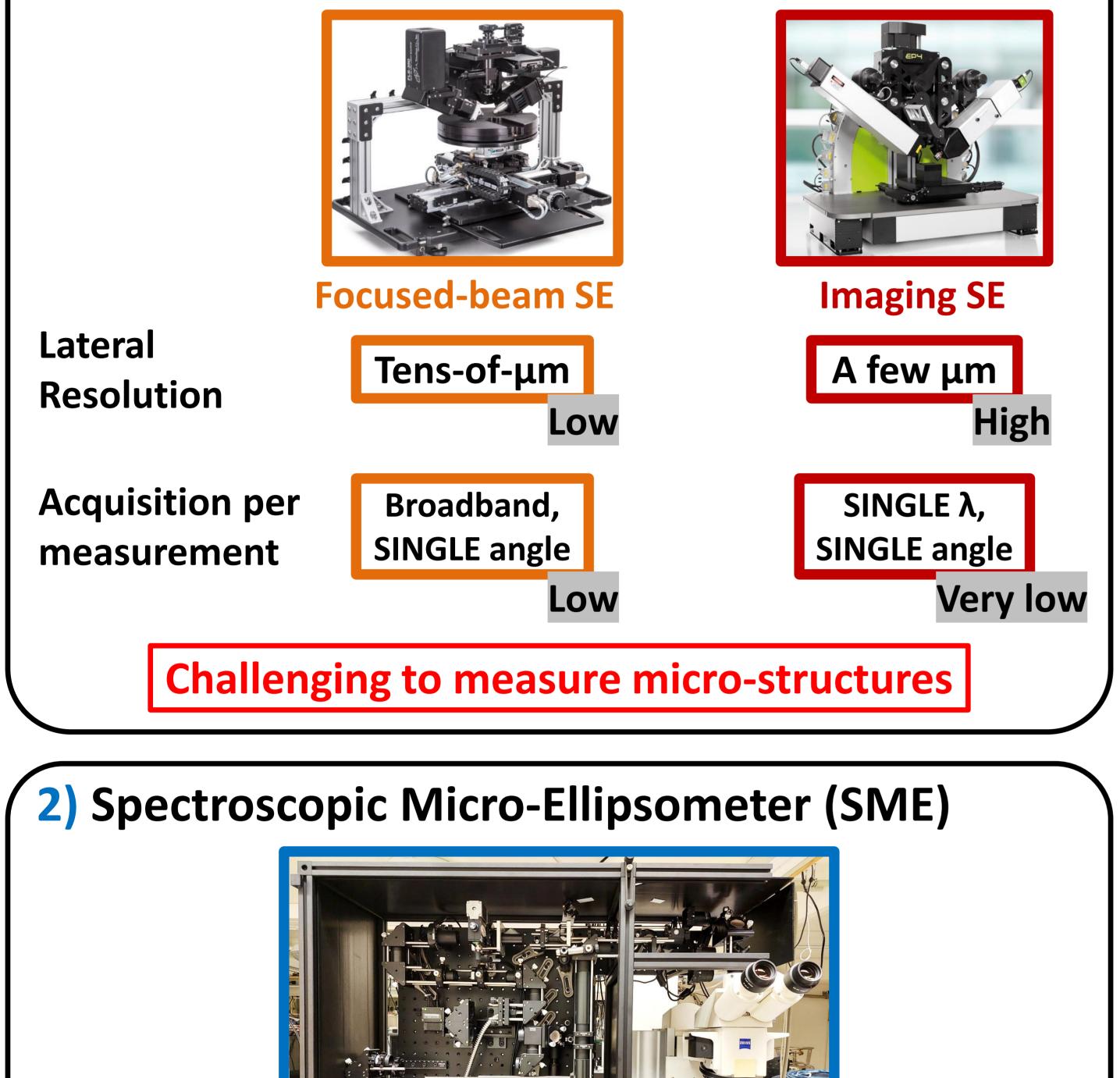
<sup>2</sup> National Institute for Materials Science, Japan

## **1)** Spectroscopic Ellipsometry

- Optical technique for thin film characterization
  - Complex refractive index (*n* and *k*)
  - Thin film thickness (sub-angstrom accuracy)

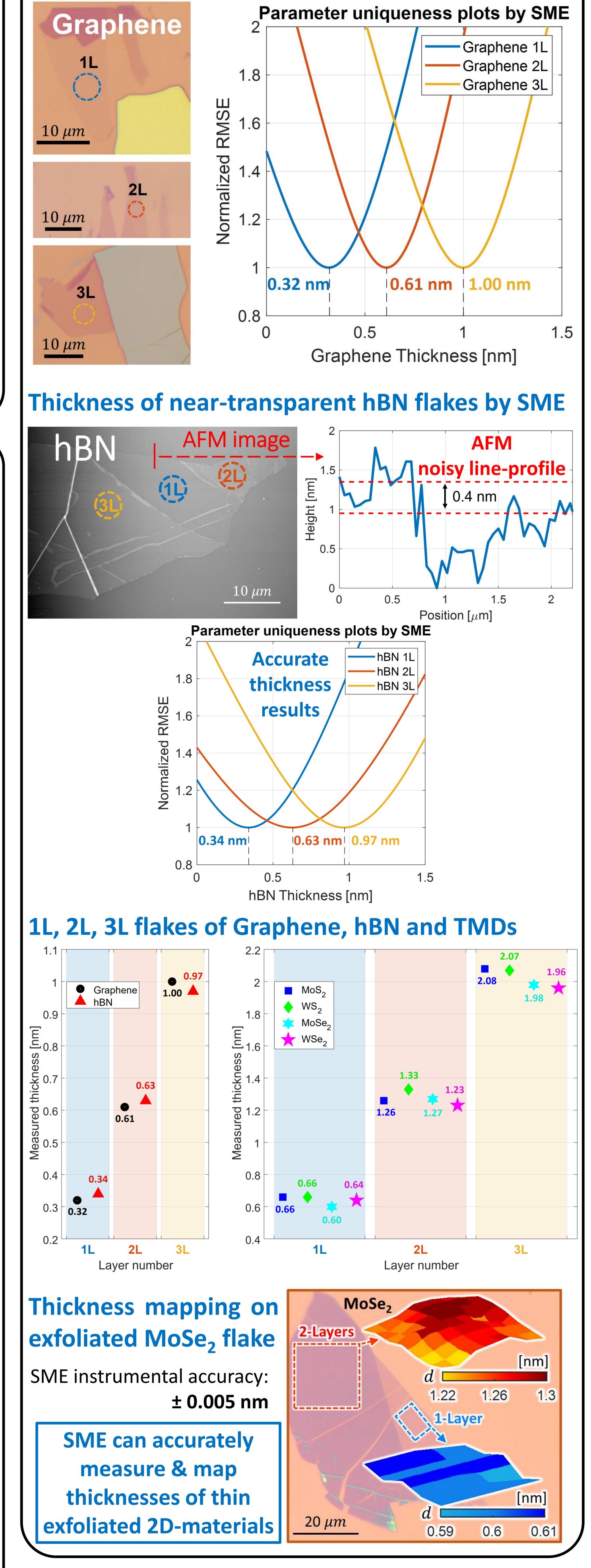
### **High lateral resolution Spectroscopic Ellipsometers (SEs)**

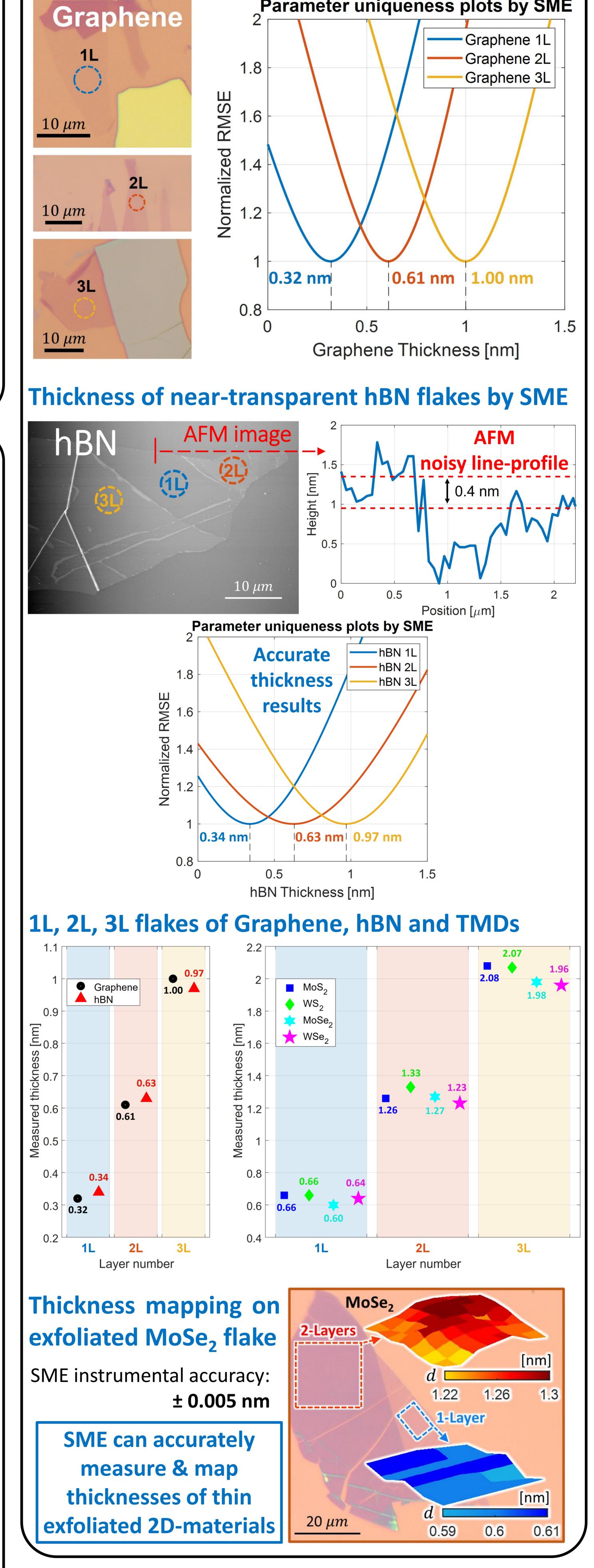


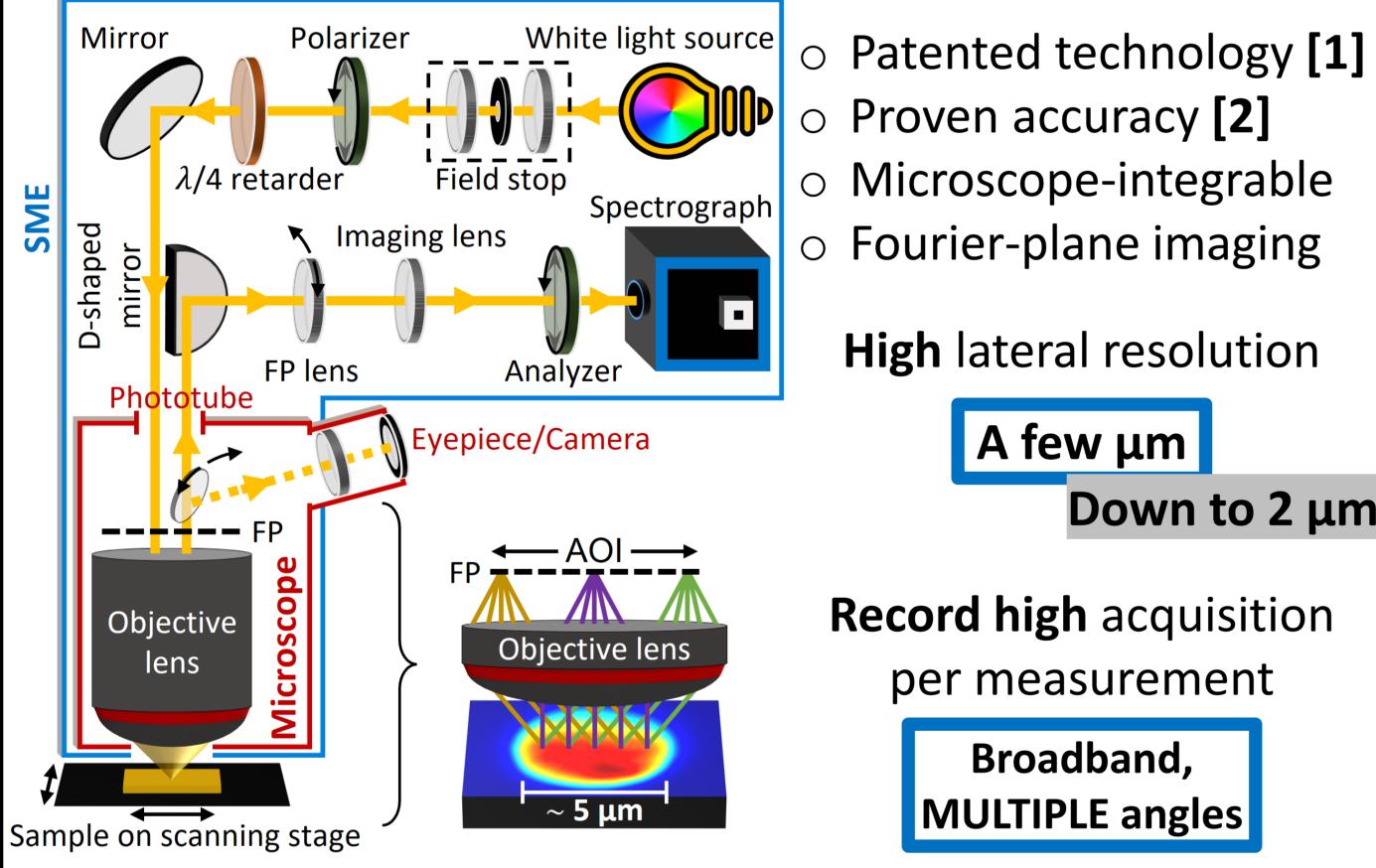


# **3)** Thickness of exfoliated vdW materials [3]

• Parameter uniqueness plot: Error between SME data and model, when the model is scanned for flake's thickness



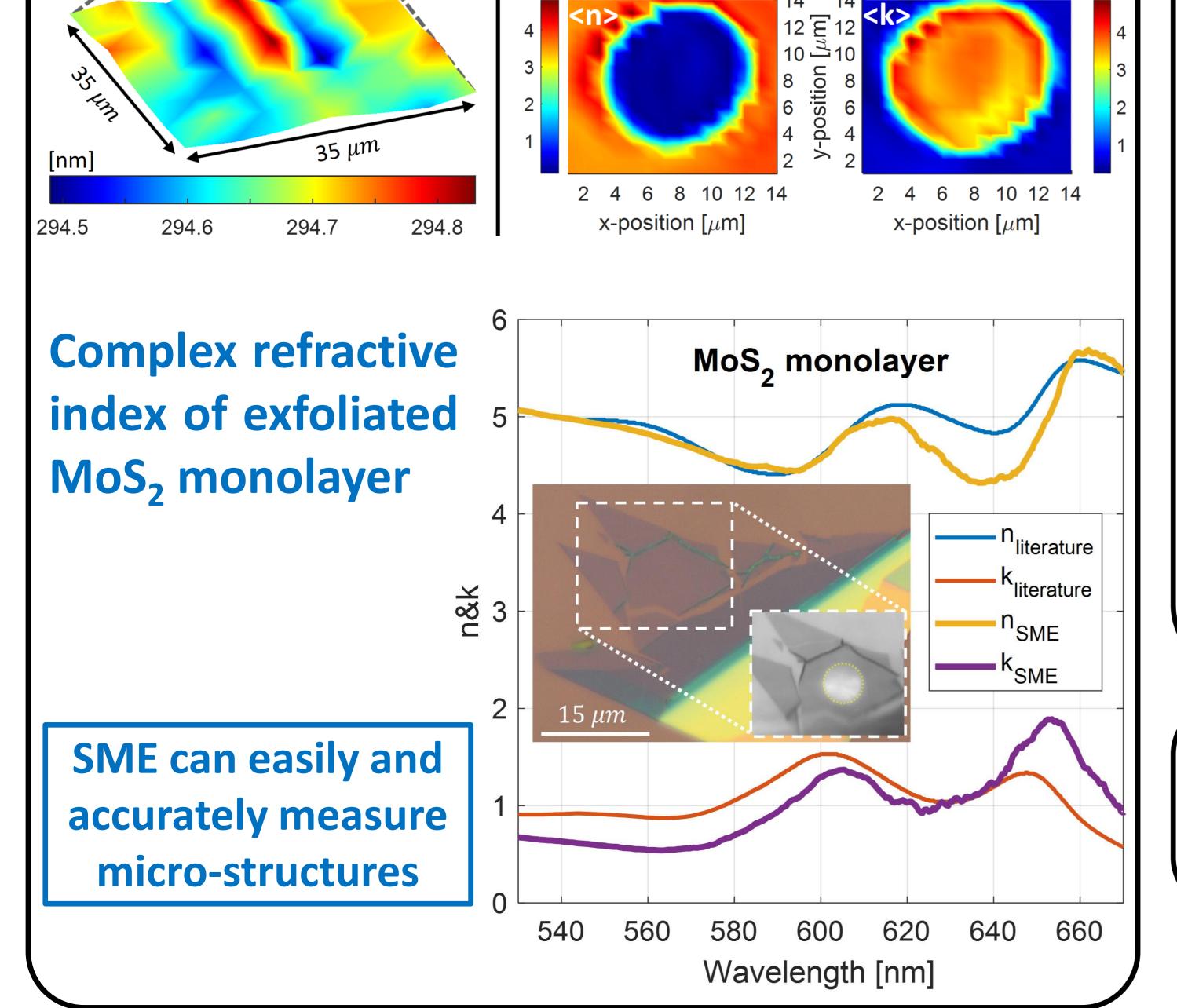




SiO<sub>2</sub> thickness mapping

## • Microscope-integrable • Fourier-plane imaging **High** lateral resolution A few µm Down to 2 µm **Record high** acquisition per measurement Broadband, MULTIPLE angles **High lateral resolution mappings** Pseudo complex refractive index mapping Golo $r = 5 \mu m$

Silicon



### References

[1] R. Kenaz and R. Rapaport, United States Patent No. 11,262,293 B2, 2022.

- [2] R. Kenaz and R. Rapaport, arXiv:2207.14161, 2022.
- **[3]** R. Kenaz et al., **arXiv:2211.07437**, 2022.



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